### TetraFET

# D2006UK

METAL GATE RF SILICON FET

# GOLD METALLISED MULTI-PURPOSE SILICON DMOS RF FET 15W – 28V – 1GHz PUSH–PULL

### FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- VERY LOW C<sub>rss</sub>
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN 13 dB MINIMUM

### **APPLICATIONS**

• HF/VHF/UHF COMMUNICATIONS from DC to 2 GHz

## **ABSOLUTE MAXIMUM RATINGS** (T<sub>case</sub> = 25°C unless otherwise stated)

P <sub>D</sub>	Power Dissipation	70W
BV <sub>DSS</sub>	Drain – Source Breakdown Voltage *	65V
BV <sub>GSS</sub>	Gate – Source Breakdown Voltage *	±20V
I <sub>D(sat)</sub>	Drain Current *	3A
T <sub>stg</sub>	Storage Temperature	–65 to 150°C
Тj	Maximum Operating Junction Temperature	200°C

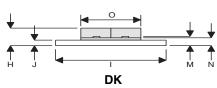
\* Per Side

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



**MECHANICAL DATA** 

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PIN 1	SOURCE (COMMON)	PIN 2	DRAIN 1
PIN 3	DRAIN 2	PIN 4	GATE 2

PIN 5 GATE 1

DIM	mm	Tol.	Inches	Tol.
Α	6.45	0.13	0.254	0.005
В	1.65R	0.13	0.065R	0.005
С	45°	5°	45°	5°
D	16.51	0.76	0.650	0.03
E	6.47	0.13	0.255	0.005
F	18.41	0.13	0.725	0.005
G	1.52	0.13	0.060	0.005
н	4.82	0.25	0.190	0.010
I	24.76	0.13	0.975	0.005
J	1.52	0.13	0.060	0.005
K	0.81R	0.13	0.032R	0.005
М	0.13	0.02	0.005	0.001
Ν	2.16	0.13	0.085	0.005



#### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

Parameter		Test Conditions		Min.	Тур.	Max.	Unit	
	PER SIDE							
BV <sub>DSS</sub>	Drain-Source	$V_{GS} = 0$	I <sub>D</sub> = 10mA	65			V	
	Breakdown Voltage			05			v	
IDSS	Zero Gate Voltage	V <sub>DS</sub> = 28V	V <sub>GS</sub> = 0			3	mA	
	Drain Current					3	IIIA	
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> = 20V	$V_{DS} = 0$			1	μA	
V <sub>GS(th)</sub>	Gate Threshold Voltage *	I <sub>D</sub> = 10mA	$V_{DS} = V_{GS}$	1		7	V	
9 <sub>fs</sub>	Forward Transconductance *	V <sub>DS</sub> = 10V	I <sub>D</sub> = 0.6A	0.54			S	
		тот	AL DEVICE					
G <sub>PS</sub>	Common Source Power Gain	P <sub>O</sub> = 15W		13			dB	
η	Drain Efficiency	V <sub>DS</sub> = 28V	I <sub>DQ</sub> = 0.6A	40			%	
VSWR	Load Mismatch Tolerance	f = 1GHz		20:1			—	
PER SIDE								
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 0$	$V_{GS} = -5V f = 1MHz$			36	pF	
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 28V	$V_{GS} = 0$ f = 1MHz			18	pF	
C <sub>rss</sub>	Reverse Transfer Capacitance	$V_{DS} = 28V$	$V_{GS} = 0$ f = 1MHz			1.5	pF	

\* Pulse Test: Pulse Duration = 300  $\mu$ s , Duty Cycle  $\leq$  2%

### HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

### THERMAL DATA

R <sub>THj-case</sub>	Thermal Resistance Junction – Case	Max. 2.5°C / W
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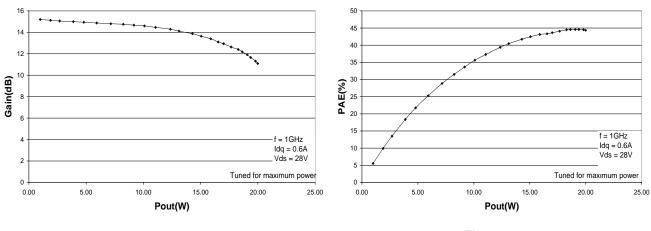
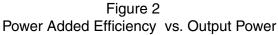


Figure 1 Gain vs. Output Power



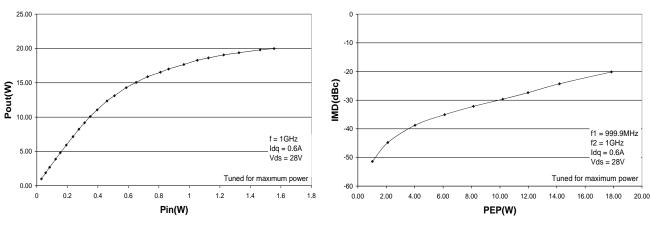
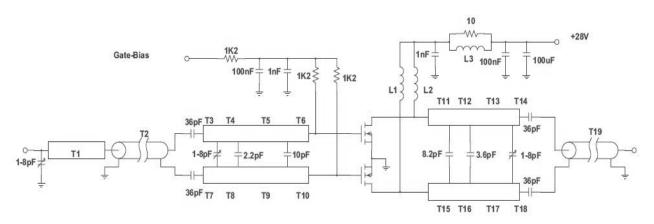


Figure 3 Output Power vs. Input Power Figure 4 IMD3 vs. PEP

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## **1000MHz TEST FIXTURE**

Substrate 0.8mm thick PTFE/glass All microstrip lines W = 2.7mm

- T1 23 mm
- T2, T19 50mm 50 OHM UT 34 semi-rigid coax
- T3, T7 6mm
- T4, T8 8mm
- T5, T9 15mm
- T6, T10 9mm
- T11,T15 8mm
- T12,T16 7mm
- T13,T17 11mm
- T14,T18 5mm
- L1,L2 6 turns of 24swg enamelled copper wire, 3mm i.d.
- L3 1.5 turns of 24swg enamelled copper wire on Siemens B62152-a7x 2 hole core

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